



N-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	60V
I_D	200A
$R_{DS(ON)}$ (at $V_{GS}=10V$)	2.9 mohm
$R_{DS(ON)}$ (at $V_{GS}=4.5V$)	3.6 mohm
100% EAS Tested	
100% V_{DS} Tested	

General Description

Split Gate Trench MOSFET technology
Excellent package for heat dissipation



YJP200G06A

Electrical Characteristics ($T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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Typical Performance Characteristics

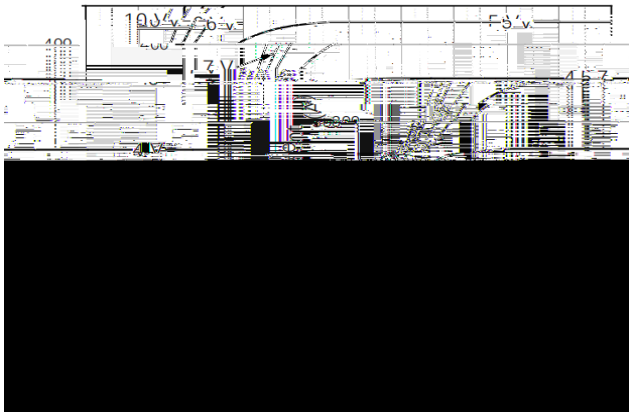


Figure1. Output Characteristics



Figure2. Transfer Characteristics

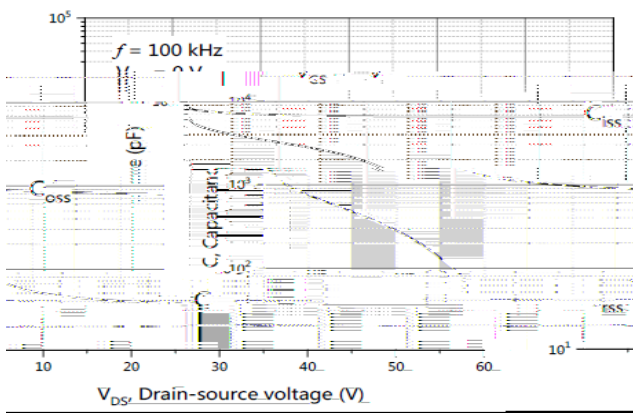


Figure3. Capacitance Characteristics

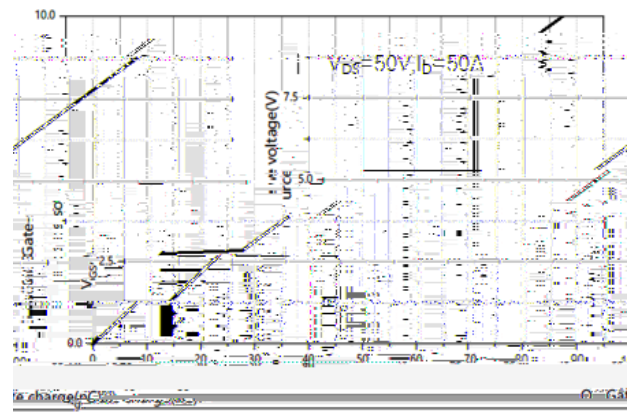


Figure4. Gate Charge

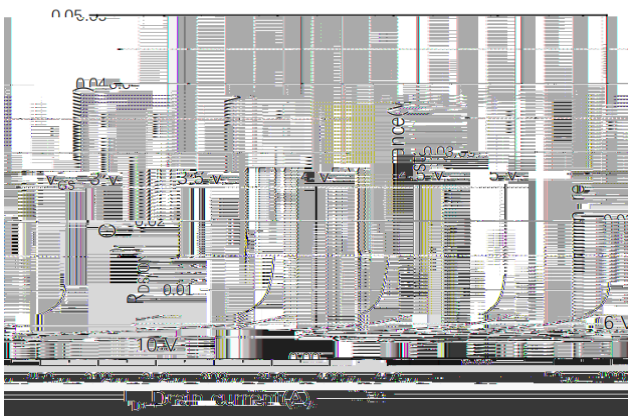


Figure5. Drain-Source on Resistance

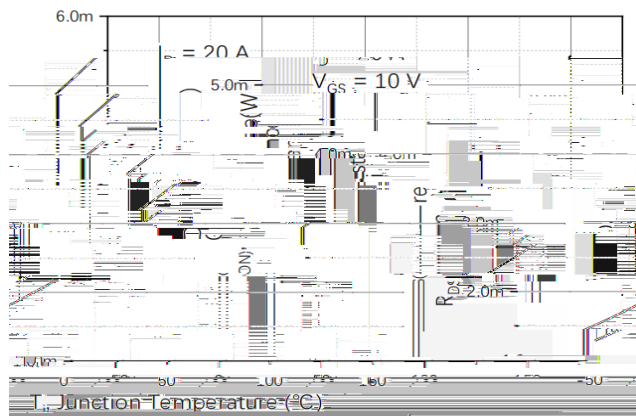


Figure6. Drain-Source on Resistance

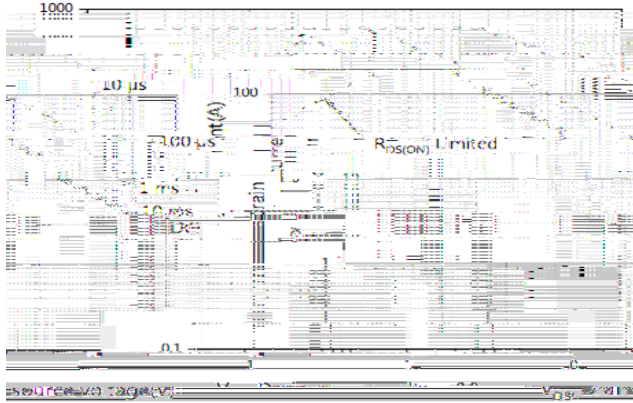


Figure7. Safe Operation Area

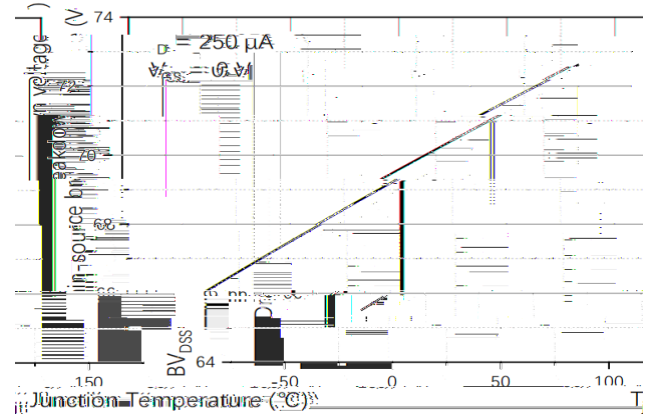


Figure8. Drain-source breakdown voltage

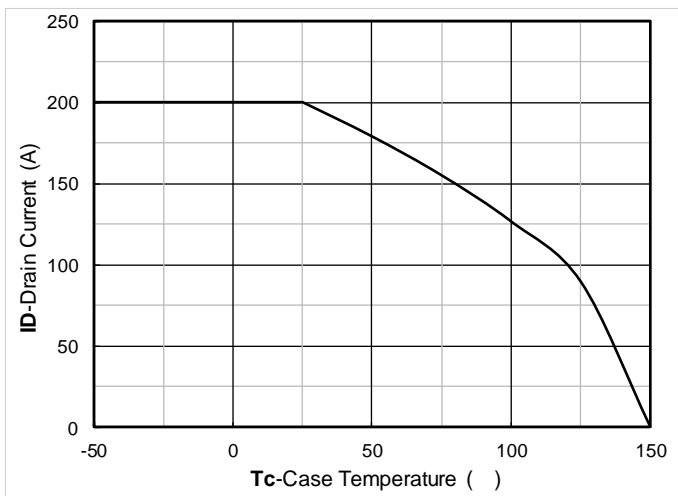
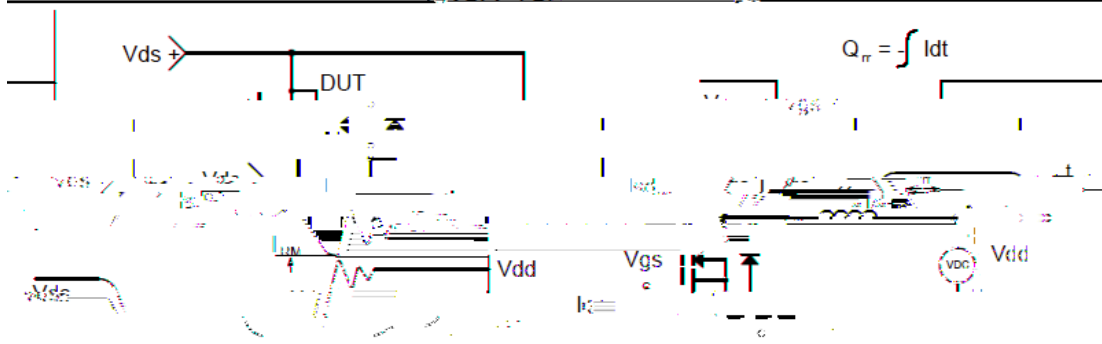


Figure 9. Current dissipation

YJP200G06A



Figure D: Diode Recovery Test Circuit & Waveforms



TO-220AB-C Package Information

NOTE:
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.

